

140 COMMERCE DRIVE **MONTGOMERYVILLE, PA** 18936-1013

PHONE: (215) 631-9840 FAX: (215) 631-9855

#### **MS2267**

#### RF & MICROWAVE TRANSISTORS **AVIONICS APPLICATIONS**

#### **Features**

- 960 1215MHz
- **50 VOLTS**
- 5:1 VSWR CAPABILITY @ RATED CONDITIONS
- **INPUT/OUTPUT MATCHING**
- $P_{OUT} = 250 WATTS$
- $G_P = 8.0 \text{ dB MINIMUM}$
- **COMMON BASE CONFIGURATION**

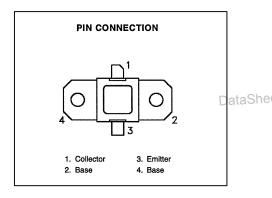
# .400 x .400 2L flanged (M214) hermetically sealed

#### **DESCRIPTION:**

The MS2267 is a high power Class C NPN transistor specifically designed for TACAN/DME applications.

This device is capable of operation under moderate pulse width and duty cycles. Low thermal resistance and computerized automatic wire bonding techniques ensure high reliability and product consistency.

The MS2267 utilizes an emitter ballasted die geometry capable of operating into a 5:1 VSWR @ 1.0 dB overdrive.



## ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
P <sub>DISS</sub>	Power Dissipation* (T <sub>C</sub> ≤ 90°C)	575	W
I <sub>C</sub>	Device Current*	20	Α
<b>V</b> cc	Collector-Supply Voltage*	50	V
<b>T</b> J	Junction Temperature (Pulsed RF Operation)	250	°C
T <sub>STG</sub>	Storage Temperature	-65 to +200	°C

#### **Thermal Data**

R <sub>TH(J-C)</sub>	Junction-case Thermal Resistance* (1)	0.28	°C/W
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<sup>\*</sup> Applies only to rated RF amplifier operation (1) Infra-red scan of hot spot junction temperature at rated RF operating conditions



# **ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC**

Symbol	Test Conditions		Value		Unit	
		Min.	Тур.	Max.	Onit	
BV <sub>CBO</sub>	I <sub>C</sub> = 35mA	I <sub>E</sub> = 0 mA	65			V
BV <sub>EBO</sub>	I <sub>E</sub> = 15mA	$I_C = 0 \text{ mA}$	4.0			V
BV <sub>CES</sub>	I <sub>C</sub> = 25mA	I <sub>B</sub> = 0 mA	60			V
I <sub>CES</sub>	V <sub>BE</sub> = 0 V	$V_{CE} = 50V$			20	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5V	I <sub>C</sub> = 1A	10			

#### **DYNAMIC**

et4U.cor **Value** DataShe **Symbol Test Conditions** Unit Min. Typ. Max. DataSheet4U.com  $P_{\text{OUT}}$ f = 960 - 1215MHz $P_{IN} = 40W$  $V_{CC} = 50V$ 250 295 W f = 960 - 1215MHz $P_{IN} = 40W$  $V_{CC} = 50V$ 38 44 % ης f = 960 - 1215MHz $P_{IN} = 40W$  $V_{CC} = 50V$ 8.0 8.7 dB G<sub>P</sub>

**Conditions:** 

Pulse width = 20  $\mu$ S

**Duty Cycle = 5%** 

 $T_C = 25^{\circ}C$ 

#### **IMPEDANCE DATA**

FREQ	$Z_IN(\Omega)$	$Z_{\mathtt{CL}}\!(\Omega)$			
960 MHz	1.0 + j3.5	1.9 – j1.8			
1090MHz	4.0 + j3.5	1.6 – j0.9			
1215MHz	2.2 + j2.2	1.4 – j1.1			

 $P_{IN} = 40W$ 

 $V_{CC} = 50V$ 

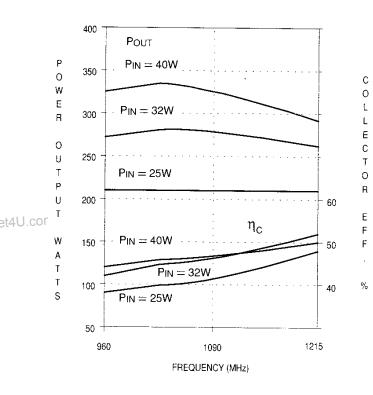
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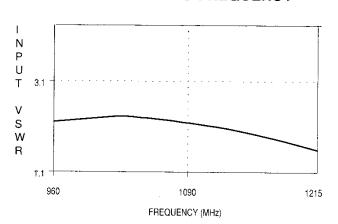


#### **TYPICAL PERFORMANCE**

# TYPICAL BROADBAND POWER AMPLIFIER



#### INPUT VSWR vs FREQUENCY



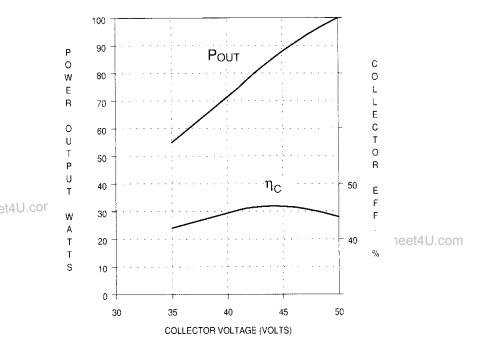
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# **TYPICAL PERFORMANCE (CONTINUED)**

# TYPICAL POWER OUTPUT & COLLECTOR EFFICIENCY vs COLLECTOR VOLTAGE



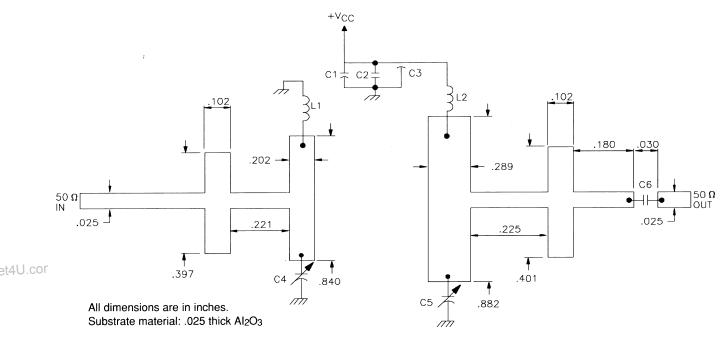
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# **TEST CIRCUIT**



: 100 µF Electrolytic Capacitor, 63V C1

: .1 µF Ceramic Capacitor C2 СЗ : Feedthru Bypass SCI 712-022

: Johanson 7475 Gigatrim .6 — 4.5 pF

Johanson 7475 Gigatrim .6 — 4.5 pF D.C. Block 100 pF C5

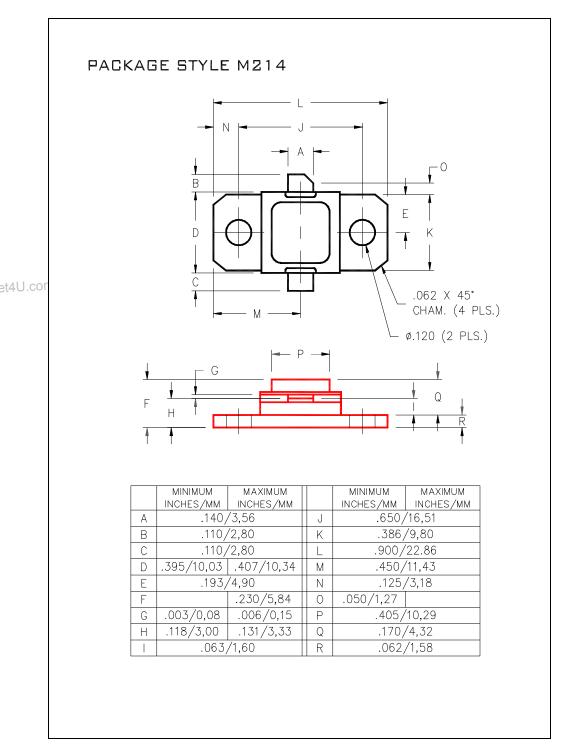
C6

#26 Wire, 4 Turn .062 I.D. L1 L2 #26 Wire, 4 Turn .062 I.D.

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## PACKAGE MECHANICAL DATA



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